

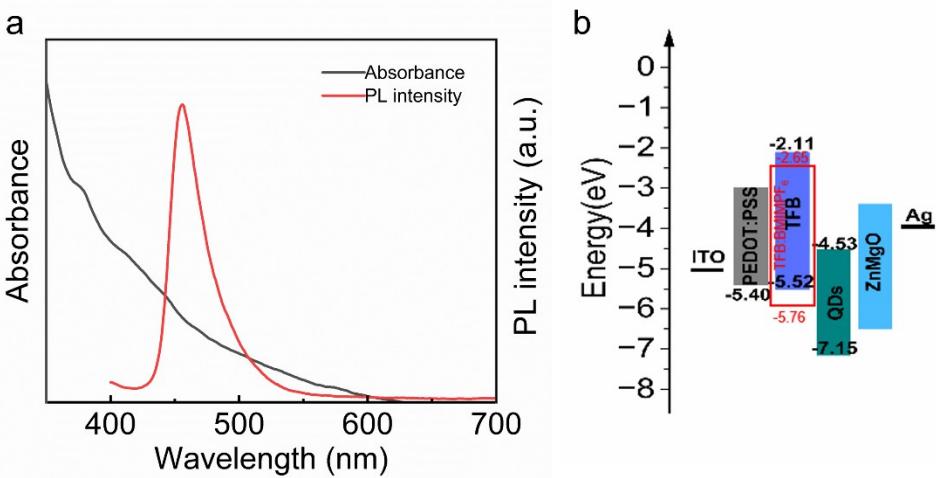
## Supporting Information

### **Enhancing Efficiency and Stability of ZnSe Pure Blue Quantum Dot Light-Emitting Diodes via Ionic Liquid Doping**

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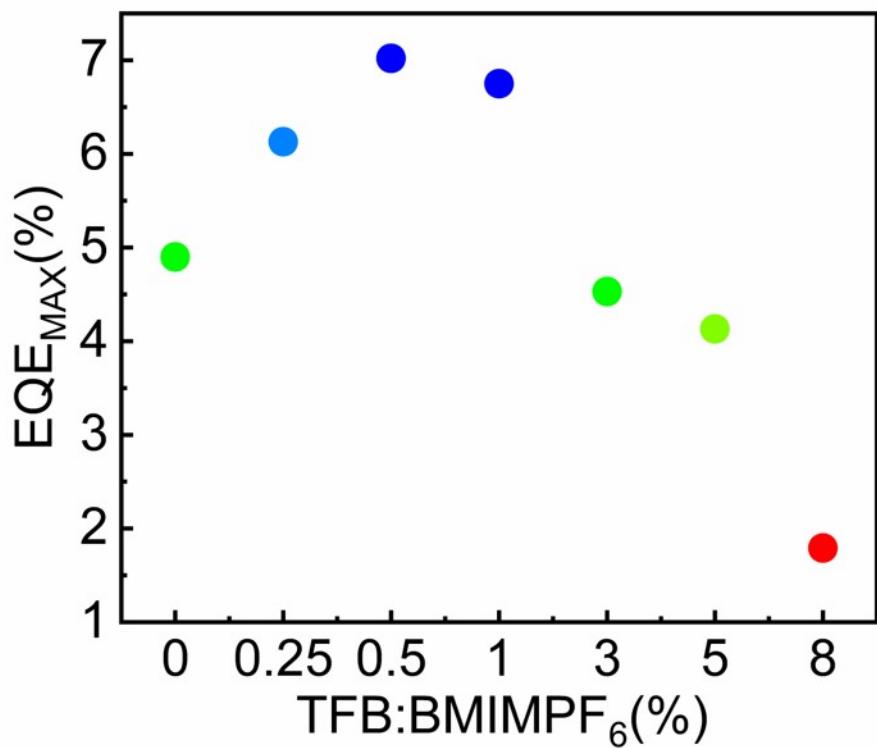
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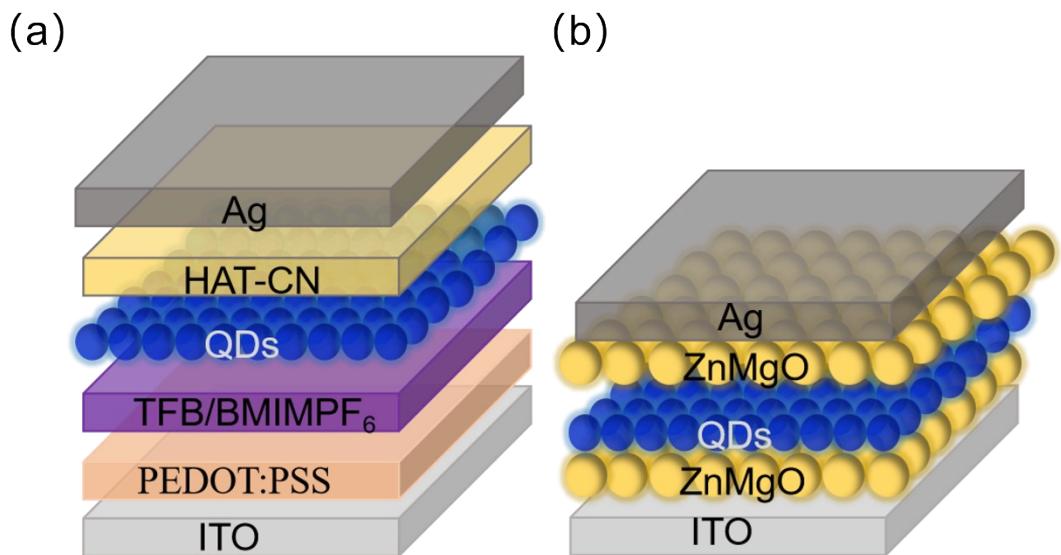
**Fig. S1** (a) Absorbance and PL of QDs. (b) Energy level diagram of QLEDs with IL treated TFB.

The PL peak centered of QDs(ZnSe/ZnS) at 456 nm and the FWHM is 33 nm.



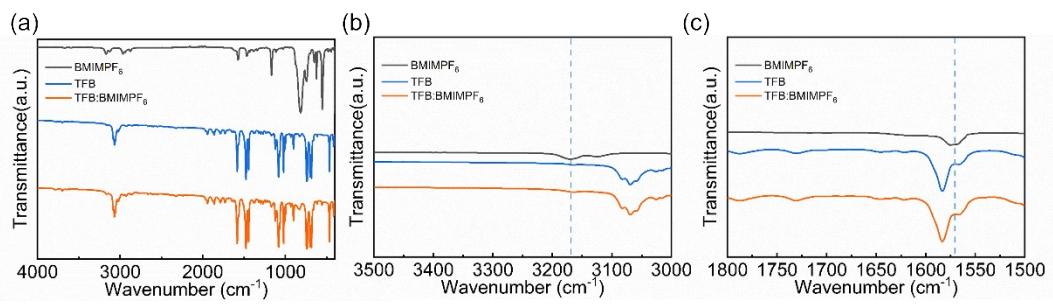
**Fig. S2** Different doping concentrations characteristics of EQEs of the QLEDs with the TFB HTLs including the BMIMPF<sub>6</sub> treated ones.

Doping different concentrations characteristics of maximum EQEs of the QLEDs is 4.90%, 6.13%, 7.02%, 6.75%, 4.53%, 4.13% and 1.79%, respectively.

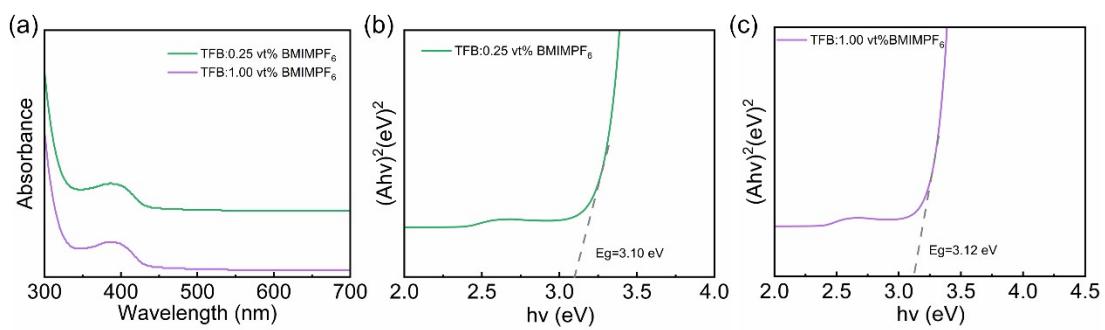


**Fig. S3** Device structure of the (a) hole-only and (b) electron-only devices.

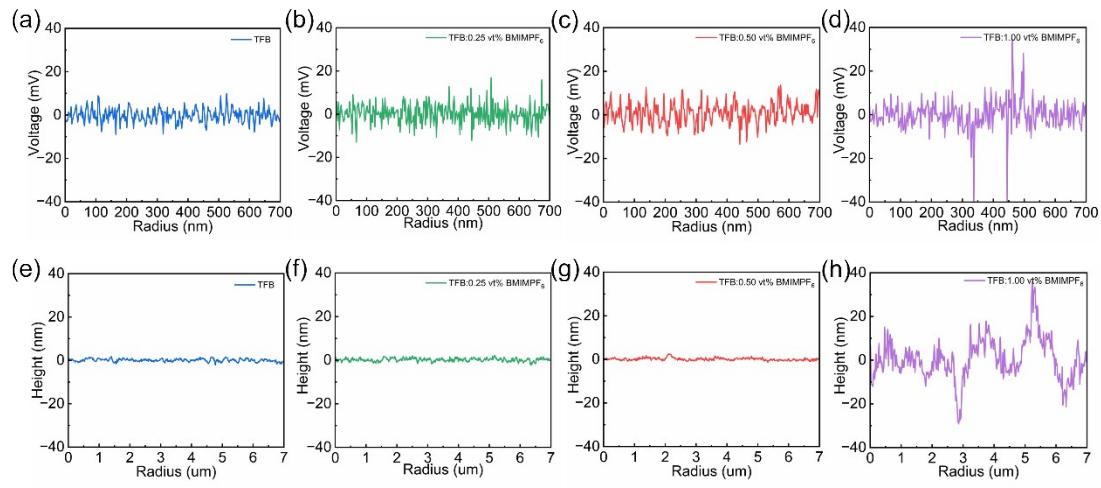
Device structure of the hole-only device is ITO/PEDOT:PSS/TFB/QDs/HAT-CN/Ag. Device structure of the hole-only device is ITO/ZnMgO/QDs/ ZnMgO /Ag.



**Fig. S4** Fourier-transform infrared (FTIR) spectra of BMIMPF<sub>6</sub> ionic liquid (IL) and TFB.



**Fig. S5** (a) Absorbance of TFB:0.25%BMIMPF<sub>6</sub> and TFB:1.00%BMIMPF<sub>6</sub> films. Tauc plots of (b) the TFB:0.25%BMIMPF<sub>6</sub> films and (d) the TFB:1.00%BMIMPF<sub>6</sub> films.



**Fig. S6** Surface potentials of a) the TFB films, b) the TFB:0.25%BMIMPF<sub>6</sub> films, c) the TFB:0.50%BMIMPF<sub>6</sub> films and d) the TFB:1.00%BMIMPF<sub>6</sub> films. Surface morphologies of e) the TFB films, f) the TFB:0.25%BMIMPF<sub>6</sub> films, g) the TFB:0.50%BMIMPF<sub>6</sub> films and h) the TFB:1.00%BMIMPF<sub>6</sub> films.

**Table S1:** A list of the performance of QLEDs.

	Turn-on voltage (V <sub>on</sub> ) @ 1 cd m <sup>-2</sup>	Driving voltage (V) @ 100 cd m <sup>-2</sup>	Maximum current efficiency (cd A-1)	Maximum EQE (%) @ 100 cd m <sup>-2</sup> (Luminance (cd m <sup>-2</sup> ) @ 9V)	EQE (%) @ 100 cd m <sup>-2</sup>	EQE (%) / Luminance (cd m <sup>-2</sup> ) @ 9V
<b>TFB</b>	5.2	7.6	5.40	4.90 @ 277	4.39	4.40/733
<b>TFB with 0.25%</b> <b>BMIMPF<sub>6</sub></b>	5.4	6.8	6.19	6.13 @ 1029	2.50	5.91/1670
<b>TFB with 0.50%</b> <b>BMIMPF<sub>6</sub></b>	5.2	7.0	7.09	7.02 @ 486	5.34	6.52/1305
<b>TFB with 1.00%</b> <b>BMIMPF<sub>6</sub></b>	5.0	6.8	6.79	6.75 @ 966	3.85	6.58/1440

**Table S2:** A list of the resistance and capacitance in the equivalent circuit of corresponding Nyquist plots.

	<b>R(<math>\Omega</math>)</b>	<b>Rtr(<math>\Omega</math>)</b>	<b>CPE1(F)</b>	<b>Rrec(<math>\Omega</math>)</b>	<b>CPE2(F)</b>
<b>TFB</b>	185	3.83 e <sup>4</sup>	8.104 e <sup>-9</sup>	4.323 e <sup>6</sup>	2.559 e <sup>-9</sup>
<b>TFB with 0.50%</b>	283.9	3.285 e <sup>5</sup>	1.746 e <sup>-6</sup>	8843	2.927 e <sup>-9</sup>
<b>BMIMPF<sub>6</sub></b>					